

# John Cressler

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/1565922/publications.pdf>

Version: 2024-02-01

336  
papers

3,943  
citations

201385

27  
h-index

276539

41  
g-index

337  
all docs

337  
docs citations

337  
times ranked

1986  
citing authors

#	ARTICLE	IF	CITATIONS
1	Design Methodology for a Wideband, Low Insertion Loss, Digital Step Attenuator in SiGe BiCMOS Technology. IEEE Transactions on Circuits and Systems II: Express Briefs, 2022, 69, 744-748.	2.2	5
2	Radiation Hardened Millimeter-Wave Receiver Implemented in 90-nm, SiGe HBT Technology. IEEE Transactions on Nuclear Science, 2022, 69, 2154-2161.	1.2	2
3	A Millimeter-Wave, Transformer-Based, SiGe Distributed Attenuator. IEEE Microwave and Wireless Components Letters, 2022, 32, 145-148.	2.0	7
4	Response of Integrated Silicon Microwave <i>pin</i> Diodes to X-Ray and Fast-Neutron Irradiation. IEEE Transactions on Nuclear Science, 2022, 69, 282-289.	1.2	0
5	Modeling Transient Loss Due to Ionizing Particles in Silicon Photonic Waveguides. IEEE Transactions on Nuclear Science, 2022, 69, 518-526.	1.2	1
6	Using Machine Learning to Mitigate Single-Event Upsets in RF Circuits and Systems. IEEE Transactions on Nuclear Science, 2022, 69, 381-389.	1.2	1
7	Single-Event Transients in a Commercially Available, Integrated Germanium Photodiode for Silicon Photonic Systems. IEEE Transactions on Nuclear Science, 2022, 69, 527-533.	1.2	1
8	Total-Ionizing-Dose Response of SiGe HBTs at Elevated Temperatures. IEEE Transactions on Nuclear Science, 2022, 69, 1079-1084.	1.2	1
9	Voltage-Controlled Oscillator Utilizing Inverse-Mode SiGe-HBT Biasing Circuit for the Mitigation of Single-Event Effects. IEEE Transactions on Nuclear Science, 2022, 69, 1242-1248.	1.2	2
10	An Efficient, Broadband SiGe HBT Non-Uniform Distributed Power Amplifier Leveraging a Compact, Two-Section $\lambda/4$ Output Impedance Transformer. IEEE Transactions on Microwave Theory and Techniques, 2022, 70, 3524-3533.	2.9	4
11	A D-Band Reflective-Type Phase Shifter Using a SiGe PIN Diode Resonant Load. IEEE Microwave and Wireless Components Letters, 2022, 32, 1191-1194.	2.0	5
12	A Compact, Low Loss, and Broadband Two-Section Lumped-Element Wilkinson Power Combiner Using 130 nm SiGe HBT BiCMOS Technology. , 2022, , .		0
13	Triaxial Balun With Inherent Harmonic Reflection for Millimeter-Wave Frequency Doublers. IEEE Transactions on Microwave Theory and Techniques, 2021, 69, 2822-2831.	2.9	8
14	Localized Excitation of Silicon Photonic Waveguides for Measurement of Free-Carrier Lifetime and Surface Recombination Velocity. , 2021, , .		1
15	High Responsivity Ge Phototransistor in Commercial CMOS Si-Photonics Platform for Monolithic Optoelectronic Receivers. IEEE Electron Device Letters, 2021, 42, 196-199.	2.2	6
16	Variability of p-n Junctions and SiGe HBTs at Cryogenic Temperatures. IEEE Transactions on Electron Devices, 2021, 68, 987-993.	1.6	5
17	Operation of Current Mirrors in SiGe BiCMOS Technology at Cryogenic Temperatures. IEEE Transactions on Electron Devices, 2021, 68, 1439-1445.	1.6	5
18	A New Emitter-Base-Collector-Base-Emitter SiGe HBT for High Power, Single-Pole Double-Throw X-Band Switches. IEEE Electron Device Letters, 2021, 42, 465-468.	2.2	4

#	ARTICLE	IF	CITATIONS
19	Integrated Silicon Photonics for Enabling Next-Generation Space Systems. <i>Photonics</i> , 2021, 8, 131.	0.9	18
20	Optical Single-Event Transients Induced in Integrated Silicon-Photonic Waveguides by Two-Photon Absorption. <i>IEEE Transactions on Nuclear Science</i> , 2021, 68, 785-792.	1.2	14
21	Millimeter-Wave SiGe Radiometer Front End With Transformer-Based Dicke Switch and On-Chip Calibration Noise Source. <i>IEEE Journal of Solid-State Circuits</i> , 2021, 56, 1464-1474.	3.5	7
22	Variability in Total-Ionizing-Dose Response of Fourth-Generation SiGe HBTs. <i>IEEE Transactions on Nuclear Science</i> , 2021, 68, 949-957.	1.2	7
23	Zero-Process-Change SiGe Heterojunction Avalanche Photodiode for High-Speed, High-Gain Detection Near the Silicon Band Edge. <i>IEEE Electron Device Letters</i> , 2021, 42, 1260-1263.	2.2	0
24	A 60-GHz SiGe Power Amplifier With Three-Conductor Transmission-Line-Based Wilkinson Baluns and Asymmetric Directional Couplers. <i>IEEE Transactions on Microwave Theory and Techniques</i> , 2021, 69, 709-722.	2.9	9
25	A $\nu$ -Band SiGe Power Amplifier Using a Four-Way Coupled-Line Wilkinson Combiner. <i>IEEE Microwave and Wireless Components Letters</i> , 2021, 31, 1239-1242.	2.0	19
26	Analysis of the Impact of Radiation-Induced Optical Transients on Deep-Space Optical Communications Systems using PPM. , 2021, , .		0
27	Performance Improvements of Reverse-Saturated SiGe HBT Millimeter-Wave Switches with Floating Emitter Configuration. , 2021, , .		0
28	A 24 GHz SiGe HBT Cascode Non-uniform Distributed Power Amplifier Using A Compact, Wideband Two-Section Lumped Element Output Impedance Transformer. , 2021, , .		4
29	A S/C/X/Ku-band, 4-Tap, Digitally Controllable Analog FIR Filter with Reconfigurable Bandwidth and RF Filtering Profile. , 2021, , .		0
30	Dynamic Behavior of Breakdown Mechanisms in SiGe HBTs. , 2021, , .		1
31	An Efficient Wideband 94 GHz On-Chip Air-Cavity Backed Planar Inverted-F Antenna. , 2021, , .		0
32	Dual-Band Millimeter-Wave Quadrature LO Generation With a Common-Centroid Floorplan. <i>IEEE Transactions on Circuits and Systems II: Express Briefs</i> , 2020, 67, 260-264.	2.2	1
33	Response of Waveguide-Integrated Germanium-on-Silicon p-i-n Photodiodes to Neutron Displacement Damage. <i>IEEE Transactions on Nuclear Science</i> , 2020, 67, 296-304.	1.2	6
34	Comparison of Single-Event Transients in SiGe HBTs on Bulk and Thick-Film SOI. <i>IEEE Transactions on Nuclear Science</i> , 2020, 67, 71-80.	1.2	7
35	New Approach for Pulsed-Laser Testing That Mimics Heavy-Ion Charge Deposition Profiles. <i>IEEE Transactions on Nuclear Science</i> , 2020, 67, 81-90.	1.2	16
36	Electronic-to-Photonic Single-Event Transient Propagation in a Segmented Mach-Zehnder Modulator in a Si/SiGe Integrated Photonics Platform. <i>IEEE Transactions on Nuclear Science</i> , 2020, 67, 260-267.	1.2	3

#	ARTICLE	IF	CITATIONS
37	Single-Event Transients in SiGe HBTs Induced by Pulsed X-Ray Microbeam. IEEE Transactions on Nuclear Science, 2020, 67, 91-98.	1.2	4
38	A D-band SiGe Frequency Doubler with a Harmonic Reflector Embedded in a Triaxial Balun. , 2020, , .		4
39	Investigation of $\pi$ -Doubler Technique to Improve RF Performance of Inverse-Mode SiGe HBTs. IEEE Microwave and Wireless Components Letters, 2020, 30, 873-875.	2.0	5
40	A Balanced Power Amplifier with Asymmetric Coupled-Line Couplers and Wilkinson Baluns in a 90 nm SiGe BiCMOS Technology. , 2020, , .		2
41	A New Wideband, Low Insertion Loss, High Linearity SiGe RF Switch. IEEE Microwave and Wireless Components Letters, 2020, 30, 985-988.	2.0	23
42	An investigation on dose rate effect of $^{60}\text{Co}$ gamma radiation on 200 GHz SiGe HBTs. AIP Conference Proceedings, 2020, , .	0.3	0
43	A SiGe Millimeter-Wave Front-End for Remote Sensing and Imaging. , 2020, , .		3
44	Mitigation of Single-Event Effects in SiGe-HBT Current-Mode Logic Circuits. Sensors, 2020, 20, 2581.	2.1	1
45	A Two-Way Wideband Active SiGe BiCMOS Power Divider/Combiner for Reconfigurable Phased Arrays With Controllable Beam Width. IEEE Access, 2020, 8, 2578-2589.	2.6	2
46	Cryogenic characterization of a ferroelectric field-effect-transistor. Applied Physics Letters, 2020, 116, .	1.5	19
47	Tradeoffs Between RF Performance and SET Robustness in Low-Noise Amplifiers in a Complementary SiGe BiCMOS Platform. IEEE Transactions on Nuclear Science, 2020, 67, 1521-1529.	1.2	3
48	A 60-GHz SiGe Radiometer Calibration Switch Utilizing a Coupled Avalanche Noise Source. IEEE Microwave and Wireless Components Letters, 2020, 30, 417-420.	2.0	18
49	Highly Linear High-Power 802.11ac/ax WLAN SiGe HBT Power Amplifiers With a Compact 2nd-Harmonic-Shorted Four-Way Transformer and a Thermally Compensating Dynamic Bias Circuit. IEEE Journal of Solid-State Circuits, 2020, 55, 2356-2370.	3.5	26
50	Design of an 18-50 GHz SiGe HBT Cascode Non-uniform Distributed Power Amplifier. , 2020, , .		1
51	Physics of Hot Carrier Degradation Under Saturation Mode Operation in SiGe HBTs. , 2020, , .		0
52	A New Wideband, Low Insertion Loss SiGe Digital Step Attenuator A New Wideband, Low Insertion Loss SiGe Digital Step Attenuator. , 2020, , .		2
53	A W-Band SiGe Transceiver with Built-in Self-Test. , 2019, , .		2
54	A Compact, High-Power, 60 GHz SPDT Switch Using Shunt-Series SiGe PIN Diodes. , 2019, , .		6

#	ARTICLE	IF	CITATIONS
55	Increasing the signal-to-noise ratio of magnetic tunnel junctions by cryogenic preamplification. Journal of Applied Physics, 2019, 125, 163902.	1.1	2
56	Total Ionizing Dose Effects in 70-GHz Bandwidth Photodiodes in a SiGe Integrated Photonics Platform. IEEE Transactions on Nuclear Science, 2019, 66, 125-133.	1.2	11
57	Cryogenic Characterization of Antiferroelectric Zirconia down to 50 mK. , 2019, , .		2
58	DC and RF Variability of SiGe HBTs Operating Down to Deep Cryogenic Temperatures. , 2019, , .		6
59	Reliability Differences Between SiGe HBTs Optimized for High-Performance and Medium-Breakdown. , 2019, , .		1
60	A 2-20 GHz SiGe Amplitude Control Circuit with Differential Signal Selectivity for Wideband Reconfigurable Electronics. , 2019, , .		1
61	Optimizing Optical Parameters to Facilitate Correlation of Laser- and Heavy-Ion-Induced Single-Event Transients in SiGe HBTs. IEEE Transactions on Nuclear Science, 2019, 66, 359-367.	1.2	15
62	The Effects of Temperature on the Single-Event Transient Response of a High-Voltage (>30 V) Complementary SiGe-on-SOI Technology. IEEE Transactions on Nuclear Science, 2019, 66, 389-396.	1.2	1
63	Best Practices for Using Electrostatic Discharge Protection Techniques for Single-Event Transient Mitigation. IEEE Transactions on Nuclear Science, 2019, 66, 240-247.	1.2	3
64	Using Bessel beams and two-photon absorption to predict radiation effects in microelectronics. Optics Express, 2019, 27, 37652.	1.7	9
65	A 0.32-THz SiGe Imaging Array With Polarization Diversity. IEEE Transactions on Terahertz Science and Technology, 2018, 8, 215-223.	2.0	18
66	Single-Event Upset Mitigation in a Complementary SiGe HBT BiCMOS Technology. IEEE Transactions on Nuclear Science, 2018, 65, 231-238.	1.2	7
67	Limiting Effects on the Design of Vertical Superjunction Collectors in SiGe HBTs. IEEE Transactions on Electron Devices, 2018, 65, 793-797.	1.6	0
68	A Highly Efficient X-Band Inverse Class-F SiGe HBT Cascode Power Amplifier With Harmonic-Tuned Wilkinson Power Combiner. IEEE Transactions on Circuits and Systems II: Express Briefs, 2018, 65, 1609-1613.	2.2	16
69	p-n-p-Based RF Switches for the Mitigation of Single-Event Transients in a Complementary SiGe BiCMOS Platform. IEEE Transactions on Nuclear Science, 2018, 65, 391-398.	1.2	6
70	Utilizing SiGe HBT Power Detectors for Sensing Single-Event Transients in RF Circuits. IEEE Transactions on Nuclear Science, 2018, 65, 239-248.	1.2	8
71	An Electrostatic Discharge Protection Circuit Technique for the Mitigation of Single-Event Transients in SiGe BiCMOS Technology. IEEE Transactions on Nuclear Science, 2018, 65, 426-431.	1.2	4
72	Design and Analysis of a Low Loss, Wideband Digital Step Attenuator With Minimized Amplitude and Phase Variations. IEEE Journal of Solid-State Circuits, 2018, 53, 2202-2213.	3.5	57

#	ARTICLE	IF	CITATIONS
73	Hot-Carrier-Damage-Induced Current Gain Enhancement (CGE) Effects in SiGe HBTs. IEEE Transactions on Electron Devices, 2018, 65, 2430-2438.	1.6	11
74	Experimental Validation of an Equivalent LET Approach for Correlating Heavy-Ion and Laser-Induced Charge Deposition. IEEE Transactions on Nuclear Science, 2018, 65, 1724-1733.	1.2	25
75	A Compact Highly Efficient High-Power Ka-band SiGe HBT Cascode Frequency Doubler With Four-Way Input Transformer Balun. IEEE Transactions on Microwave Theory and Techniques, 2018, 66, 2879-2887.	2.9	19
76	Cryogenic Characterization of RF Low-Noise Amplifiers Utilizing Inverse-Mode SiGe HBTs for Extreme Environment Applications. IEEE Transactions on Device and Materials Reliability, 2018, 18, 613-619.	1.5	0
77	A 28-GHz SiGe Bootstrapped Gilbert Frequency Doubler With 26.2% PAE. IEEE Microwave and Wireless Components Letters, 2018, 28, 1122-1124.	2.0	9
78	A V-Band SiGe Image-Reject Receiver Front-End for Atmospheric Remote Sensing. , 2018, , .		6
79	A 160 GHz Distributed, Stacked SiGe Power Amplifier. , 2018, , .		1
80	Using SiGe-on-SOI HBTs to Build 300°C Capable Analog Circuits. , 2018, , .		1
81	A Low-Loss Broadband Quadrature Signal Generation Network for High Image Rejection at Millimeter-Wave Frequencies. IEEE Transactions on Microwave Theory and Techniques, 2018, 66, 5336-5346.	2.9	13
82	A Comparison of Electron, Proton and Gamma Irradiation Effects on the I-V Characteristics of 200 GHz SiGe HBTs. IEEE Transactions on Device and Materials Reliability, 2018, 18, 592-598.	1.5	13
83	A SiGe-BiCMOS Wideband Active Bidirectional Digital Step Attenuator With Bandwidth Tuning and Equalization. IEEE Transactions on Microwave Theory and Techniques, 2018, 66, 3866-3876.	2.9	13
84	Collector Transport in SiGe HBTs Operating at Cryogenic Temperatures. IEEE Transactions on Electron Devices, 2018, 65, 3697-3703.	1.6	15
85	Potential Limitations on Integrated Silicon Photonic Waveguides Operating in a Heavy Ion Environment. IEEE Transactions on Nuclear Science, 2018, 65, 141-148.	1.2	18
86	SiGe HBT Profiles With Enhanced Inverse-Mode Operation and Their Impact on Single-Event Transients. IEEE Transactions on Nuclear Science, 2018, 65, 399-406.	1.2	9
87	A 28-GHz Switchless, SiGe Bidirectional Amplifier Using Neutralized Common-Emitter Differential Pair. IEEE Microwave and Wireless Components Letters, 2018, 28, 717-719.	2.0	6
88	On the Application of Inverse-Mode SiGe HBTs in RF Receivers for the Mitigation of Single-Event Transients. IEEE Transactions on Nuclear Science, 2017, 64, 1142-1150.	1.2	9
89	Modeling Single-Event Transient Propagation in a SiGe BiCMOS Direct-Conversion Receiver. IEEE Transactions on Nuclear Science, 2017, , 1-1.	1.2	6
90	A 0.3-15 GHz SiGe LNA With >1 THz Gain-Bandwidth Product. IEEE Microwave and Wireless Components Letters, 2017, 27, 380-382.	2.0	11

#	ARTICLE	IF	CITATIONS
91	Operation of SiGe HBTs Down to 70 mK. IEEE Electron Device Letters, 2017, 38, 12-15.	2.2	28
92	Single-Event Effects in High-Frequency Linear Amplifiers: Experiment and Analysis. IEEE Transactions on Nuclear Science, 2017, 64, 125-132.	1.2	5
93	The Impact of Technology Scaling on the Single-Event Transient Response of SiGe HBTs. IEEE Transactions on Nuclear Science, 2017, 64, 406-414.	1.2	22
94	Physical Differences in Hot Carrier Degradation of Oxide Interfaces in Complementary (n-p-n+p-n-p) SiGe HBTs. IEEE Transactions on Electron Devices, 2017, 64, 37-44.	1.6	10
95	Using TCAD Modeling to Compare Heavy-Ion and Laser-Induced Single Event Transients in SiGe HBTs. IEEE Transactions on Nuclear Science, 2017, 64, 398-405.	1.2	24
96	Single-Event Effects in a Millimeter-Wave Receiver Front-End Implemented in 90 nm, 300 GHz SiGe HBT Technology. IEEE Transactions on Nuclear Science, 2017, 64, 536-543.	1.2	5
97	An X-band inverse class-F SiGe HBT cascode power amplifier With harmonic-tuned output transformer. , 2017, , .		12
98	An Investigation of High-Temperature (to 300 Å°C) Safe-Operating-Area in a High-Voltage Complementary SiGe on SOI Technology. IEEE Transactions on Electron Devices, 2017, 64, 3748-3755.	1.6	5
99	Total Ionizing Dose Effects on a High-Voltage (>30V) Complementary SiGe on SOI Technology. IEEE Transactions on Nuclear Science, 2017, 64, 277-284.	1.2	5
100	Single-Event Transient Response of Comparator Pre-Amplifiers in a Complementary SiGe Technology. IEEE Transactions on Nuclear Science, 2017, 64, 89-96.	1.2	8
101	The Use of Inverse-Mode SiGe HBTs as Active Gain Stages in Low-Noise Amplifiers for the Mitigation of Single-Event Transients. IEEE Transactions on Nuclear Science, 2017, 64, 359-366.	1.2	8
102	5â€‰MeV Proton irradiation effects on 200â€‰GHz siliconâ€‰germanium heterojunction bipolar transistors. Radiation Effects and Defects in Solids, 2017, 172, 922-930.	0.4	2
103	Micronimbus: A cubesat temperature profilometer for the earth's atmosphere using a single-chip 60 GHz siGe radiometer. , 2017, , .		2
104	A 19â€‰34 GHz SiGe HBT square-law detector with ultra-low 1/f noise for atmospheric radiometers. , 2017, , .		2
105	Recovery of electrical characteristics of 80â€‰.MeV carbon ion irradiated SiGe HBTs by mixed mode electrical stress. AIP Conference Proceedings, 2017, , .	0.3	0
106	Modeling single-event transient propagation in a SiGe BiCMOS direct-conversion receiver. , 2016, , .		1
107	SiGe Technology as a Millimeter-Wave Platform: Scaling Issues, Reliability Physics, Circuit Performance, and New Opportunities. , 2016, , .		5
108	A highly-efficient 138â€‰170 GHz SiGe HBT frequency doubler for power-constrained applications. , 2016, , .		23



#	ARTICLE	IF	CITATIONS
109	A SiGe-BiCMOS Wideband (2-22 GHz) Active Power Divider/Combiner Circuit Supporting Bidirectional Operation. IEEE Transactions on Microwave Theory and Techniques, 2016, 64, 4676-4684.	2.9	12
110	An Investigation of the Use of Inverse-Mode SiGe HBTs as Switching Pairs for SET-Mitigated RF Mixers. IEEE Transactions on Nuclear Science, 2016, 63, 1099-1108.	1.2	13
111	A Compact, Wideband Lumped-Element Wilkinson Power Divider/Combiner Using Symmetric Inductors with Embedded Capacitors. IEEE Microwave and Wireless Components Letters, 2016, 26, 595-597.	2.0	19
112	Design and On-Wafer Characterization of X-Band SiGe HBT Low-Noise Amplifiers. IEEE Transactions on Microwave Theory and Techniques, 2016, 64, 3631-3642.	2.9	27
113	Inverse class-F X-band SiGe HBT power amplifier with 44% PAE and 24.5 dBm peak output power. Microwave and Optical Technology Letters, 2016, 58, 2868-2871.	0.9	1
114	Co-design of a SiGe BiCMOS X-band, asymmetric, low insertion loss, high power handling SPDT Switch and an Ultra Low Noise LNA for next-generation T/R modules. , 2016, , .		3
115	Beyond the boundaries: Enabling new circuit opportunities by using SiGe HBTs in counterintuitive ways. , 2016, , .		2
116	A Compact, Active SiGe Power Divider With Multi-Octave Bandwidth. IEEE Microwave and Wireless Components Letters, 2016, 26, 945-947.	2.0	6
117	The effects of hot carrier and swift heavy ion irradiation on electrical characteristics of advanced 200-300 GHz SiGe HBTs. AIP Conference Proceedings, 2016, , .	0.3	0
118	An Active Bi-Directional SiGe DPDT Switch With Multi-Octave Bandwidth. IEEE Microwave and Wireless Components Letters, 2016, 26, 279-281.	2.0	13
119	An Investigation of Single-Event Effect Modeling Techniques for a SiGe RF Low-Noise Amplifier. IEEE Transactions on Nuclear Science, 2016, 63, 273-280.	1.2	16
120	Advantages of utilizing through-silicon vias in SiGe HBT RF low-noise amplifier design. Microwave and Optical Technology Letters, 2015, 57, 2703-2706.	0.9	1
121	Optimization of SiGe HBT RF Switches for Single-Event Transient Mitigation. IEEE Transactions on Nuclear Science, 2015, 62, 3057-3063.	1.2	8
122	An Investigation of the SET Response of Devices and Differential Pairs in a 32-nm SOI CMOS Technology. IEEE Transactions on Nuclear Science, 2015, 62, 2643-2649.	1.2	1
123	Single-Event Effects in a W-Band (75-110 GHz) Radar Down-Conversion Mixer Implemented in 90-nm, 300 GHz SiGe HBT Technology. IEEE Transactions on Nuclear Science, 2015, 62, 2657-2665.	1.2	12
124	The Role of Negative Feedback Effects on Single-Event Transients in SiGe HBT Analog Circuits. IEEE Transactions on Nuclear Science, 2015, 62, 2599-2605.	1.2	4
125	A SiGe D-Band Low-Noise Amplifier Utilizing Gain-Boosting Technique. IEEE Microwave and Wireless Components Letters, 2015, 25, 61-63.	2.0	35
126	On the Cryogenic RF Linearity of SiGe HBTs in a Fourth-Generation 90-nm SiGe BiCMOS Technology. IEEE Transactions on Electron Devices, 2015, 62, 1127-1135.	1.6	5



#	ARTICLE	IF	CITATIONS
127	Bias- and Temperature-Dependent Accumulated Stress Modeling of Mixed-Mode Damage in SiGe HBTs. IEEE Transactions on Electron Devices, 2015, 62, 2084-2091.	1.6	19
128	A Comparison of Field and Current-Driven Hot-Carrier Reliability in NPN SiGe HBTs. IEEE Transactions on Electron Devices, 2015, 62, 2244-2250.	1.6	19
129	Large-Signal Reliability Analysis of SiGe HBT Cascode Driver Amplifiers. IEEE Transactions on Electron Devices, 2015, 62, 1383-1389.	1.6	28
130	A comparison of 100ÂMeV oxygen ion and 60Co gamma irradiation effects on advanced 200ÂGHz SiGe heterojunction bipolar transistors. Indian Journal of Physics, 2015, 89, 789-796.	0.9	7
131	A D-Band Micromachined End-Fire Antenna in 130-nm SiGe BiCMOS Technology. IEEE Transactions on Antennas and Propagation, 2015, 63, 2449-2459.	3.1	65
132	A Comparison of the Degradation in RF Performance Due to Device Interconnects in Advanced SiGe HBT and CMOS Technologies. IEEE Transactions on Electron Devices, 2015, 62, 1803-1810.	1.6	50
133	The reliability studies of nano-engineered SiGe HBTs using Pelletron accelerator. AIP Conference Proceedings, 2015, , .	0.3	1
134	A Class-E Tuned W-Band SiGe Power Amplifier With 40.4% Power-Added Efficiency at 93 GHz. IEEE Microwave and Wireless Components Letters, 2015, 25, 663-665.	2.0	26
135	A W-band integrated silicon-germanium loop-back and front-end transmit-receive switch for Built-in-self-test. , 2015, , .		4
136	High-performance W-band LNA and SPDT switch in 0.13&#x00B5;m SiGe HBT technology. , 2015, , .		0
137	80 MeV Carbon Ion Irradiation Effects On Advanced 200 GHz Silicon-germanium Heterojunction Bipolar Transistors. Advanced Materials Letters, 2015, 6, 120-126.	0.3	7
138	Impact of Total Ionizing Dose on a 4th Generation, 90Ânm SiGe HBT Gaussian Pulse Generator. IEEE Transactions on Nuclear Science, 2014, 61, 3050-3054.	1.2	10
139	Single-Event Transient and Total Dose Response of Precision Voltage Reference Circuits Designed in a 90-nm SiGe BiCMOS Technology. IEEE Transactions on Nuclear Science, 2014, 61, 3210-3217.	1.2	22
140	W-band SiGe power amplifiers. , 2014, , .		11
141	Compact, low-power, single-ended and differential SiGe W-band LNAs. , 2014, , .		0
142	Ultra-low noise and low power 18.7 GHz radiometer LNAs in a 0.5 THz SiGe technology utilizing back-side etched inductors. , 2014, , .		1
143	An Investigation of Single-Event Transients in C-SiGe HBT on SOI Current Mirror Circuits. IEEE Transactions on Nuclear Science, 2014, 61, 3193-3200.	1.2	15
144	On the cryogenic performance of ultra-low-loss, wideband SPDT RF switches designed in a 180 nm SOI-CMOS technology. , 2014, , .		1

#	ARTICLE	IF	CITATIONS
145	An investigation of $f_{T}$ and $f_{max}$ degradation due to device interconnects in 0.5 THz SiGe HBT technology. , 2014, , .		3
146	Systematic methodology for applying Mason's signal flow graph to analysis of feedback circuits. , 2014, , .		1
147	Evaluation of Enhanced Low Dose Rate Sensitivity in Fourth-Generation SiGe HBTs. IEEE Transactions on Nuclear Science, 2014, 61, 2915-2922.	1.2	18
148	On the Transient Response of a Complementary (npn & formula formulatype="inline"&gt;&lt;tex>T_j ETQq0 0 0 rgBT /Overlock 10 Tf 50 Transactions on Nuclear Science, 2014, 61, 3146-3153.	1.2	15
149	Design of Radiation-Hardened RF Low-Noise Amplifiers Using Inverse-Mode SiGe HBTs. IEEE Transactions on Nuclear Science, 2014, 61, 3218-3225.	1.2	34
150	Mitigation of Total Dose Performance Degradation in an 8â€“18ÂGHz SiGe Reconfigurable Receiver. IEEE Transactions on Nuclear Science, 2014, 61, 3226-3235.	1.2	4
151	A high gain, W-band SiGe LNA with sub-4.0 dB noise figure. , 2014, , .		17
152	Compact, low-power, single-ended and differential SiGe W-band LNAs. , 2014, , .		0
153	A digitally-controlled seven-state X-band SiGe variable gain low noise amplifier. , 2014, , .		4
154	A 1.0 V, 10â€“22 GHz, 4 mW LNA Utilizing Weakly Saturated SiGe HBTs for Single-Chip, Low-Power, Remote Sensing Applications. IEEE Microwave and Wireless Components Letters, 2014, 24, 890-892.	2.0	17
155	Evaluating the Effects of Single Event Transients in FET-Based Single-Pole Double-Throw RF Switches. IEEE Transactions on Nuclear Science, 2014, 61, 756-765.	1.2	12
156	On the reliability of SiGe HBT cascode driver amplifiers. , 2014, , .		3
157	A high-power, low-loss W-band SPDT switch using SiGe PIN diodes. , 2014, , .		35
158	A 314 GHz, fully-integrated SiGe transmitter and receiver with integrated antenna. , 2014, , .		15
159	A Low-Loss and High Isolation D-Band SPDT Switch Utilizing Deep-Saturated SiGe HBTs. IEEE Microwave and Wireless Components Letters, 2014, 24, 400-402.	2.0	37
160	On the Analysis and Design of Low-Loss Single-Pole Double-Throw W-Band Switches Utilizing Saturated SiGe HBTs. IEEE Transactions on Microwave Theory and Techniques, 2014, 62, 2755-2767.	2.9	132
161	Advanced SiGe BiCMOS Technology for Multi-Mrad Electronic Systems. IEEE Transactions on Device and Materials Reliability, 2014, 14, 844-848.	1.5	22
162	A switchable-core SiGe HBT low-noise amplifier for millimeter-wave radiometer applications. , 2014, , .		2

#	ARTICLE	IF	CITATIONS
163	A 94 GHz, 1.4 dB Insertion Loss Single-Pole Double-Throw Switch Using Reverse-Saturated SiGe HBTs. IEEE Microwave and Wireless Components Letters, 2014, 24, 56-58.	2.0	37
164	A SiGe 8 $\mu$ m 18-GHz Receiver With Built-In-Testing Capability for Self-Healing Applications. IEEE Transactions on Microwave Theory and Techniques, 2014, 62, 2370-2380.	2.9	10
165	Impact of Technology Scaling in sub-100-nm nMOSFETs on Total-Dose Radiation Response and Hot-Carrier Reliability. IEEE Transactions on Nuclear Science, 2014, 61, 1426-1432.	1.2	15
166	A 0.8 THz $f_{m\text{MAX}}$ SiGe HBT Operating at 4.3 K. IEEE Electron Device Letters, 2014, 35, 151-153.	2.2	60
167	Low phase noise and high output power 367 GHz and 154 GHz signal sources in 130 nm SiGe HBT technology. , 2014, , .		19
168	An Investigation of Single Event Transient Response in 45-nm and 32-nm SOI RF-CMOS Devices and Circuits. IEEE Transactions on Nuclear Science, 2013, 60, 4405-4411.	1.2	18
169	In situ investigation of 75-MeV boron and 100-MeV oxygen ion irradiation effects on 50-GHz silicon-germanium heterojunction bipolar transistors. Radiation Effects and Defects in Solids, 2013, 168, 620-624.	0.4	6
170	A design methodology to achieve low input impedance and non-constant gain-bandwidth product in TIAs for optical communication. , 2013, , .		4
171	An Investigation on the Optimization and Scaling of Complementary SiGe HBTs. IEEE Transactions on Electron Devices, 2013, 60, 34-41.	1.6	4
172	Operating Voltage Constraints in 45-nm SOI nMOSFETs and Cascode Cores. IEEE Transactions on Electron Devices, 2013, 60, 132-139.	1.6	5
173	Radiation Effects in SiGe Technology. IEEE Transactions on Nuclear Science, 2013, 60, 1992-2014.	1.2	127
174	Integrated, digitally controlled, 64-element SiGe on multilayer organic X-band phased-array receiver antenna for snow measurements. IEEE Aerospace and Electronic Systems Magazine, 2013, 28, 26-39.	2.3	1
175	An Investigation of Total Ionizing Dose Damage on a Pulse Generator Intended for Space-Based Impulse Radio UWB Transceivers. IEEE Transactions on Nuclear Science, 2013, 60, 2605-2610.	1.2	3
176	Total Ionizing Dose Response of Triple-Well FET-Based Wideband, High-Isolation RF Switches in a 130 nm SiGe BiCMOS Technology. IEEE Transactions on Nuclear Science, 2013, 60, 2567-2573.	1.2	12
177	An Investigation of Single-Event Effects and Potential SEU Mitigation Strategies in Fourth-Generation, 90-nm SiGe BiCMOS. IEEE Transactions on Nuclear Science, 2013, 60, 4175-4183.	1.2	20
178	Welcome to a New T-ED Editor. IEEE Transactions on Electron Devices, 2013, 60, 5-5.	1.6	4
179	Predicting large-signal CML gate delay using Y-Parameters for fast process optimization. , 2013, , .		1
180	A compact, transformer-based 60 GHz SPDT RF switch utilizing diode-connected SiGe HBTs. , 2013, , .		11

#	ARTICLE	IF	CITATIONS
181	Integrated silicon-germanium electronics for CubeSat-based radiometers. , 2013, , .		7
182	An on-chip SiGe HBT characterization circuit for use in self-healing RF systems. , 2013, , .		1
183	Packaging Effects of Multiple X-Band SiGe LNAs Embedded in an Organic LCP Substrate. IEEE Transactions on Components, Packaging and Manufacturing Technology, 2012, 2, 1351-1360.	1.4	10
184	Analysis and design of a 3&#x2013;26 GHz low-noise amplifier in SiGe HBT technology. , 2012, , .		11
185	On-die self-healing of mixer image-rejection ratio for mixed-signal electronic systems. , 2012, , .		1
186	Structured epitaxial graphene on SiC. , 2012, , .		1
187	A new approach to designing electronic systems for operation in extreme environments: Part I - The SiGe Remote Sensor Interface. IEEE Aerospace and Electronic Systems Magazine, 2012, 27, 25-34.	2.3	11
188	A self-testable SiGe LNA and Built-in-Self-Test methodology for multiple performance specifications of RF amplifiers. , 2012, , .		2
189	An 8â€“16 GHz SiGe Low Noise Amplifier With Performance Tuning Capability for Mitigation of Radiation-Induced Performance Loss. IEEE Transactions on Nuclear Science, 2012, 59, 2837-2846.	1.2	31
190	An Ultra-Thin, High-Power, and Multilayer Organic Antenna Array With T/R Functionality in the X-Band. IEEE Transactions on Microwave Theory and Techniques, 2012, 60, 3856-3867.	2.9	11
191	A 6â€“20 GHz Adaptive SiGe Image Reject Mixer for a Self-Healing Receiver. IEEE Journal of Solid-State Circuits, 2012, 47, 1998-2006.	3.5	19
192	An X-band to Ka-band SPDT switch using 200 nm SiGe HBTs. , 2012, , .		14
193	Single-Event Response of the SiGe HBT Operating in Inverse-Mode. IEEE Transactions on Nuclear Science, 2012, 59, 2682-2690.	1.2	23
194	A New Self-Healing Methodology for RF Amplifier Circuits Based on Oscillation Principles. IEEE Transactions on Very Large Scale Integration (VLSI) Systems, 2012, 20, 1835-1848.	2.1	39
195	A V-band Differential SiGe VCO with varactor-less tuning. , 2012, , .		0
196	Establishing Best-Practice Modeling Approaches for Understanding Single-Event Transients in Gb/s SiGe Digital Logic. IEEE Transactions on Nuclear Science, 2012, 59, 958-964.	1.2	11
197	A broadband, millimeter wave, asymmetrical Marchand balun in 180 nm SiGe BiCMOS technology. , 2012, , .		9
198	Cold-capable SiGe BiCMOS wireline transceivers for distributed electronics systems. , 2012, , .		2

#	ARTICLE	IF	CITATIONS
199	A 5 GHz 0.95 dB NF Highly Linear Cascode Floating-Body LNA in 180 nm SOI CMOS Technology. IEEE Microwave and Wireless Components Letters, 2012, 22, 200-202.	2.0	50
200	Predictive TCAD modeling of the scaling-induced, reverse-biased, emitter-base tunneling current in SiGe HBTs. , 2011, , .		2
201	A UWB SiGe LNA for multi-band applications with self-healing based on DC extraction of device characteristics. , 2011, , .		4
202	Establishing best-practice modeling approaches for understanding single-event transients in Gb/s SiGe digital logic. , 2011, , .		0
203	50ÂMeV Li <sup>3+</sup> -ion irradiation effects on advanced 200ÂGHz SiGe HBTs. Radiation Effects and Defects in Solids, 2011, 166, 710-717.	0.4	14
204	An adaptive, wideband SiGe image reject mixer for a self-healing receiver. , 2011, , .		3
205	A Lightweight Organic X-Band Active Receiving Phased Array With Integrated SiGe Amplifiers and Phase Shifters. IEEE Transactions on Antennas and Propagation, 2011, 59, 100-109.	3.1	27
206	A lightweight, 64-element, organic phased array with integrated transmit-receive SiGe circuitry in the X band. , 2011, , .		1
207	A Study of Total Dose Mitigation Approaches for Charge Pumps in Phase-Locked Loop Applications. IEEE Transactions on Nuclear Science, 2011, 58, 3038-3045.	1.2	5
208	Design and Optimization of Superjunction Collectors for Use in High-Speed SiGe HBTs. IEEE Transactions on Electron Devices, 2011, 58, 1655-1662.	1.6	18
209	An Investigation of DC and RF Safe Operating Area of n-p-n \$+\$ p-n-p SiGe HBTs on SOI. IEEE Transactions on Electron Devices, 2011, 58, 2573-2581.	1.6	9
210	Trade-Offs Between RF Performance and Total-Dose Tolerance in 45-nm RF-CMOS. IEEE Transactions on Nuclear Science, 2011, 58, 2830-2837.	1.2	17
211	Design of a 250-Gbit/s SiGe HBT Electrooptic Modulator. IEEE Photonics Journal, 2011, 3, 897-914.	1.0	6
212	Fully Integrated Switch-LNA Front-End IC Design in CMOS: A Systematic Approach for WLAN. IEEE Journal of Solid-State Circuits, 2011, 46, 2613-2622.	3.5	10
213	The effect of 63ÂMeV hydrogen ion irradiation on 65ÂGHz UHV/CVD SiGe HBT BiCMOS technology. Radiation Effects and Defects in Solids, 2011, 166, 703-709.	0.4	7
214	Impact of Source/Drain contact and gate finger spacing on the RF reliability of 45-nm RF nMOSFETs. , 2011, , .		6
215	Measurement and Modeling of Carrier Transport Parameters Applicable to SiGe BiCMOS Technology Operating in Extreme Environments. IEEE Transactions on Electron Devices, 2010, 57, 551-561.	1.6	4
216	SiGe HBT CML Ring Oscillator With 2.3-ps Gate Delay at Cryogenic Temperatures. IEEE Transactions on Electron Devices, 2010, 57, 1183-1187.	1.6	6

#	ARTICLE	IF	CITATIONS
217	Design of Digital Circuits Using Inverse-Mode Cascode SiGe HBTs for Single Event Upset Mitigation. IEEE Transactions on Nuclear Science, 2010, , .	1.2	21
218	On the large-signal robustness of SiGe HBT LNAs for high-frequency wireless applications. , 2010, , .		2
219	Effects of Halo Doping and Si Capping Layer Thickness on Total-Dose Effects in Ge p-MOSFETs. IEEE Transactions on Nuclear Science, 2010, 57, 1933-1939.	1.2	15
220	Low phase noise K-Band oscillator on organic Liquid Crystal Polymer (LCP) substrate. , 2010, , .		1
221	An investigation of electro-thermal instabilities in 150 GHz SiGe HBTs fabricated on SOI. , 2010, , .		3
222	Impact of body tie and Source/Drain contact spacing on the hot carrier reliability of 45-nm RF-CMOS. , 2010, , .		6
223	A new and simple measurement approach for characterizing intermodulation distortion without using a spectrum analyzer. , 2010, , .		1
224	Influence of Interface Traps on the Temperature Sensitivity of MOSFET Drain-Current Variations. IEEE Electron Device Letters, 2010, 31, 387-389.	2.2	12
225	Charge Collection and SEU in SiGe HBT Current Mode Logic Operating at Cryogenic Temperatures. IEEE Transactions on Nuclear Science, 2010, , .	1.2	7
226	Non-TMR SEU-Hardening Techniques for SiGe HBT Shift Registers and Clock Buffers. IEEE Transactions on Nuclear Science, 2010, 57, 2119-2123.	1.2	5
227	A monolithic, wide-temperature, charge amplification channel for extreme environments. , 2010, , .		9
228	Implementation of a low cost, lightweight X-band antenna with integrated SiGe RF electronics. , 2010, , .		4
229	Mechanisms and Temperature Dependence of Single Event Latchup Observed in a CMOS Readout Integrated Circuit From 16â€³300 K. IEEE Transactions on Nuclear Science, 2010, , .	1.2	18
230	A high-linearity inverse-mode SiGe BiCMOS RF switch. , 2010, , .		7
231	A Theory of Single-Event Transient Response in Cross-Coupled Negative Resistance Oscillators. IEEE Transactions on Nuclear Science, 2010, , .	1.2	16
232	High gain, high linearity, L-band SiGe low noise amplifier with fully-integrated matching network. , 2010, , .		5
233	Reconciling 3-D Mixed-Mode Simulations and Measured Single-Event Transients in SiGe HBTs. IEEE Transactions on Nuclear Science, 2010, 57, 3342-3348.	1.2	20
234	A tunable, SiGe X-band image reject mixer. , 2010, , .		3

#	ARTICLE	IF	CITATIONS
235	On the large-signal robustness of SiGe HBT LNAs for high-frequency wireless applications. , 2010, , .		5
236	A lightweight X-band organic antenna array with integrated SiGe amplifier. , 2010, , .		5
237	Reliability of SiGe HBTs for Power Amplifiersâ€™ Part I: Large-Signal RF Performance and Operating Limits. IEEE Transactions on Device and Materials Reliability, 2009, 9, 431-439.	1.5	40
238	A Mechanism Versus SEU Impact Analysis of Collector Charge Collection in SiGe HBT Current Mode Logic. IEEE Transactions on Nuclear Science, 2009, 56, 3071-3077.	1.2	11
239	Non-TMR SEU-hardening techniques for SiGe HBT shift registers and clock buffers. , 2009, , .		0
240	Failure mechanisms in CMOS-based RF switches subjected to RF stress. , 2009, , .		8
241	SiGe digital frequency dividers with reduced residual phase noise. , 2009, , .		3
242	An investigation of electron and oxygen ion damage in Si npn RF power transistors. Radiation Effects and Defects in Solids, 2009, 164, 592-603.	0.4	15
243	On the Performance Limits of Cryogenically Operated SiGe HBTs and Its Relation to Scaling for Terahertz Speeds. IEEE Transactions on Electron Devices, 2009, 56, 1007-1019.	1.6	45
244	Compact Modeling of Mutual Thermal Coupling for the Optimal Design of SiGe HBT Power Amplifiers. IEEE Transactions on Electron Devices, 2009, , .	1.6	25
245	Compact Modeling of the Temperature Dependence of Parasitic Resistances in SiGe HBTs Down to 30 K. IEEE Transactions on Electron Devices, 2009, 56, 2169-2177.	1.6	12
246	Sub-1-K Operation of SiGe Transistors and Circuits. IEEE Electron Device Letters, 2009, 30, 508-510.	2.2	39
247	Heavy Ion Microbeam- and Broadbeam-Induced Transients in SiGe HBTs. IEEE Transactions on Nuclear Science, 2009, 56, 3078-3084.	1.2	35
248	A Ka-Band Electronically Tunable Ferroelectric Filter. IEEE Microwave and Wireless Components Letters, 2009, 19, 356-358.	2.0	25
249	A two-channel, ultra-low-power, SiGe BiCMOS receiver front-end for X-band phased array radars. , 2009, , .		10
250	A wide bandwidth sige broadband amplifier for 100 Gb/s Ethernet applications. , 2009, , .		9
251	Impact of deep trench isolation on advanced SiGe HBT reliability in radiation environments. , 2009, , .		9
252	AM/PM Nonlinearities in SiGe HBTs. , 2009, , .		1



#	ARTICLE	IF	CITATIONS
253	Junction Isolation Single Event Radiation Hardening of a 200 GHz SiGe:C HBT Technology Without Deep Trench Isolation. IEEE Transactions on Nuclear Science, 2009, 56, 3402-3407.	1.2	10
254	An Investigation of the Large-Signal RF Safe-Operating-Area on Aggressively-Biased Cascode SiGe HBTs for Power Amplifier Applications. , 2009, , .		6
255	A High-Linearity, X-Band, SiGe Low-Noise Amplifier for Improved Dynamic Range in Next-Generation Radar and Wireless Systems. , 2009, , .		6
256	A K-Band nMOS SPDT Switch and Phase Shifter Implemented in 130nm SiGe BiCMOS Technology. , 2009, , .		4
257	A Novel Device Architecture for SEU Mitigation: The Inverse-Mode Cascode SiGe HBT. IEEE Transactions on Nuclear Science, 2009, 56, 3393-3401.	1.2	22
258	Comparing RF linearity of npn and pnp SiGe HBTs. , 2009, , .		5
259	An experimental investigation of RF safe-operating-area (SOA) in SiGe HBTs on SOI. , 2009, , .		5
260	An LCP package model for use in chip/package co-design of an X-band SiGe Low Noise Amplifier. , 2009, , .		0
261	Investigation of the device design challenges and optimization issues associated with complementary SiGe HBT scaling. , 2009, , .		2
262	A novel device structure using a shared-subcollector, cascoded inverse-mode SiGe HBT for enhanced radiation tolerance. , 2009, , .		5
263	Mixed-mode stress degradation mechanisms in pnp SiGe HBTs. Reliability Physics Symposium, 2009 IEEE International, 2009, , .	0.0	5
264	A low power 1.8&#x2013;2.6 dB noise figure, SiGe HBT wideband LNA for multiband wireless applications. , 2009, , .		6
265	Cryogenic matching performance of 90 nm MOSFETs. , 2009, , .		4
266	Re-Examining TID Hardness Assurance Test Protocols for SiGe HBTs. IEEE Transactions on Nuclear Science, 2009, 56, 3318-3325.	1.2	9
267	Effects of halo doping and Si capping layer thickness on total-dose effects in Ge p-MOSFETs. , 2009, , .		0
268	Cryogenic RF Small-Signal Modeling and Parameter Extraction of SiGe HBTs. , 2009, , .		9
269	The Enhanced Role of Shallow-Trench Isolation in Ionizing Radiation Damage of 65 nm RF-CMOS on SOI. IEEE Transactions on Nuclear Science, 2009, 56, 3256-3261.	1.2	18
270	Impact of Proton Irradiation on the RF Performance of 65 nm SOI CMOS Technology. IEEE Transactions on Nuclear Science, 2009, 56, 1914-1919.	1.2	6

#	ARTICLE	IF	CITATIONS
271	SiGe HBT X-Band LNAs for Ultra-Low-Noise Cryogenic Receivers. IEEE Microwave and Wireless Components Letters, 2008, 18, 476-478.	2.0	22
272	A Silicon-Germanium Receiver for X-Band Transmit/Receive Radar Modules. IEEE Journal of Solid-State Circuits, 2008, 43, 1889-1896.	3.5	59
273	On Common-Base Avalanche Instabilities in SiGe HBTs. IEEE Transactions on Electron Devices, 2008, 55, 1276-1285.	1.6	16
274	A New Analytical Method for Robust Extraction of the Small-Signal Equivalent Circuit for SiGe HBTs Operating at Cryogenic Temperatures. IEEE Transactions on Microwave Theory and Techniques, 2008, 56, 568-574.	2.9	11
275	The Effects of Proton Irradiation on the Performance of High-Voltage n-MOSFETs Implemented in a Low-Voltage SiGe BiCMOS Platform. IEEE Transactions on Nuclear Science, 2008, 55, 3253-3258.	1.2	6
276	Performance of the SiGe HBT 8HP and 8WL Technologies after High Dose/Fluence Radiation Exposure. , 2008, , .		8
277	On the Radiation Tolerance of SiGe HBT and CMOS-Based Phase Shifters for Space-Based, Phased-Array Antenna Systems. IEEE Transactions on Nuclear Science, 2008, 55, 3246-3252.	1.2	6
278	A 12-Bit Cryogenic and Radiation-Tolerant Digital-to-Analog Converter for Aerospace Extreme Environment Applications. IEEE Transactions on Industrial Electronics, 2008, 55, 2810-2819.	5.2	18
279	Novel Total Dose and Heavy-Ion Charge Collection Phenomena in a New SiGe HBT on >Thin-Film SOI Technology. IEEE Transactions on Nuclear Science, 2008, 55, 3197-3201.	1.2	8
280	Emerging application opportunities for SiGe technology. , 2008, , .		6
281	Common-base intermodulation characteristics of advanced SiGe HBTs. , 2008, , .		6
282	Modeling mixed-mode DC and RF stress in SiGe HBT power amplifiers. , 2008, , .		8
283	Impact of proton irradiation on the RF performance of 65 nm SOI CMOS technology. , 2008, , .		0
284	The Impact of Technology Node Scaling on nMOS SPDT RE Switches. , 2008, , .		4
285	Probing Hot Carrier Phenomena in npn and pnp SiGe HBTs. , 2008, , .		5
286	Enhancing the Speed of SiGe HBTs Using fT-Doubler Techniques. , 2008, , .		14
287	A 40 GS/s SiGe track-and-hold amplifier. , 2008, , .		25
288	3-D Mixed-Mode Simulation of Single Event Transients in SiGe HBT Emitter Followers and Resultant Hardening Guidelines. IEEE Transactions on Nuclear Science, 2008, 55, 3360-3366.	1.2	12

#	ARTICLE	IF	CITATIONS
289	Laser-Induced Current Transients in Silicon-Germanium HBTs. IEEE Transactions on Nuclear Science, 2008, 55, 2936-2942.	1.2	34
290	Low Cost Organic Packaging For Silicon Based mm-wave Wireless Systems. , 2008, , .		2
291	Enhancing the Speed of SiGe HBTs Using ft-Doubler Techniques. , 2008, , .		1
292	Probing Hot Carrier Phenomena in npn and pnp SiGe HBTs. , 2008, , .		0
293	A novel base current phenomenon in SiGe HBTs operating in inverse mode. , 2007, , .		2
294	A Novel Circuit-Level SEU Hardening Technique for High-Speed SiGe HBT Logic Circuits. IEEE Transactions on Nuclear Science, 2007, 54, 2086-2091.	1.2	6
295	Comparison of Shunt and Series/Shunt nMOS Single-Pole Double-Throw Switches for X-Band Phased Array T/R Modules. , 2007, , .		18
296	Large-Signal Performance, Linearity, and Reliability Characteristics of Aggressively-Biased Cascode SiGe HBTs for Power Amplifier Applications. Bipolar/BiCMOS Circuits and Technology Meeting, IEEE Proceedings of the, 2007, , .	0.0	10
297	A Generalized SiGe HBT Single-Event Effects Model for On-Orbit Event Rate Calculations. IEEE Transactions on Nuclear Science, 2007, 54, 2322-2329.	1.2	27
298	A 2 mW, Sub-2 dB Noise Figure, SiGe Low-Noise Amplifier For X-band High-Altitude or Space-based Radar Applications. Radio Frequency Integrated Circuits (RFIC) Symposium, IEEE, 2007, , .	0.0	28
299	A Monolithic 5-Bit SiGe BiCMOS Receiver for X-Band Phased-Array Radar Systems. Bipolar/BiCMOS Circuits and Technology Meeting, IEEE Proceedings of the, 2007, , .	0.0	11
300	Source dependence and technology scaling effects on the radiation tolerance of SiGe HBTs at extreme dose and fluence levels. , 2007, , .		4
301	Understanding Radiation- and Hot Carrier-Induced Damage Processes in SiGe HBTs Using Mixed-Mode Electrical Stress. IEEE Transactions on Nuclear Science, 2007, 54, 1938-1945.	1.2	14
302	A New Current-Sweep Method for Assessing the Mixed-Mode Damage Spectrum of SiGe HBTs. IEEE Transactions on Device and Materials Reliability, 2007, 7, 479-487.	1.5	15
303	Radiation response of SiGe BiCMOS mixed-signal circuits intended for emerging lunar applications. , 2007, , .		7
304	Using SiGe technology in extreme environments. , 2007, , .		4
305	Addressing challenges in device-circuit modeling for extreme environments of space. , 2007, , .		11
306	An Exploration of Substrate Coupling at K-Band Between a SiGe HBT Power Amplifier and a SiGe HBT Voltage-Controlled-Oscillator. IEEE Microwave and Wireless Components Letters, 2007, 17, 349-351.	2.0	7

#	ARTICLE	IF	CITATIONS
307	On the Frequency Limits of SiGe HBTs for TeraHertz Applications. Bipolar/BiCMOS Circuits and Technology Meeting, IEEE Proceedings of the, 2007, , .	0.0	17
308	The Effects of X-Ray and Proton Irradiation on a 200 GHz/90 GHz Complementary \$(npn + pnp)\$ SiGe:C HBT Technology. IEEE Transactions on Nuclear Science, 2007, 54, 2190-2195.	1.2	18
309	3-D Simulation of SEU Hardening of SiGe HBTs Using Shared Dummy Collector. IEEE Transactions on Nuclear Science, 2007, 54, 2330-2337.	1.2	21
310	A comparison of 63 MeV proton and 10 keV X-ray radiation effects in 4H-SiC depletion-mode vertical trench JFETs. , 2007, , .		1
311	A Comparison of the Effects of X-Ray and Proton Irradiation on the Performance of SiGe Precision Voltage References. IEEE Transactions on Nuclear Science, 2007, 54, 2238-2244.	1.2	15
312	SiGe HBT compact modeling for extreme temperatures. , 2007, , .		12
313	The Radiation Tolerance of Strained Si/SiGe n-MODFETs. IEEE Transactions on Nuclear Science, 2007, 54, 2251-2256.	1.2	3
314	Assessing the High-Temperature Capabilities of SiGe HBTs Fabricated on CMOS-compatible Thin-film SOI. Bipolar/BiCMOS Circuits and Technology Meeting, IEEE Proceedings of the, 2007, , .	0.0	3
315	The Effects of Proton and X-Ray Irradiation on the DC and AC Performance of Complementary (npn +) Tj ETQq1 1 0,784314 rgBT /Ove	1.2	17
316	Proton-induced SEU in SiGe digital logic at cryogenic temperatures. , 2007, , .		4
317	The Application of RHBD to n-MOSFETs Intended for Use in Cryogenic-Temperature Radiation Environments. IEEE Transactions on Nuclear Science, 2007, 54, 2100-2105.	1.2	17
318	An Investigation of Negative Differential Resistance and Novel Collectorâ€“Current Kink Effects in SiGe HBTs Operating at Cryogenic Temperatures. IEEE Transactions on Electron Devices, 2007, 54, 504-516.	1.6	10
319	Impact of Scaling on the Inverse-Mode Operation of SiGe HBTs. IEEE Transactions on Electron Devices, 2007, 54, 1492-1501.	1.6	17
320	The Effects of Scaling and Bias Configuration on Operating-Voltage Constraints in SiGe HBTs for Mixed-Signal Circuits. IEEE Transactions on Electron Devices, 2007, 54, 1605-1616.	1.6	20
321	A High-Linearity 5-bit, X-band SiGe HBT Phase Shifter. , 2006, , .		12
322	Substrate Engineering Concepts to Mitigate Charge Collection in Deep Trench Isolation Technologies. IEEE Transactions on Nuclear Science, 2006, 53, 3298-3305.	1.2	39
323	Reliability Issues in SiGe HBTs Fabricated on CMOS-Compatible Thin-Film SOI. , 2006, , .		2
324	A 70 MHz - 4.1 GHz 5th-Order Elliptic gm-C Low-Pass Filter in Complementary SiGe Technology. , 2006, , .		8

#	ARTICLE	IF	CITATIONS
325	An Investigation of Dose Rate and Source Dependent Effects in 200 GHz SiGe HBTs. IEEE Transactions on Nuclear Science, 2006, 53, 3166-3174.	1.2	46
326	Proton Tolerance of SiGe Precision Voltage References for Extreme Temperature Range Electronics. IEEE Transactions on Nuclear Science, 2006, 53, 3210-3216.	1.2	21
327	Evaluation of the Radiation Tolerance of SiGe Heterojunction Bipolar Transistors Under 24-GeV Proton Exposure. IEEE Transactions on Nuclear Science, 2006, 53, 3889-3893.	1.2	18
328	Analysis of Factors Contributing to Common-Base Avalanche Instabilities in Advanced SiGe HBTs. Bipolar/BiCMOS Circuits and Technology Meeting, IEEE Proceedings of the, 2006, , .	0.0	2
329	The Effects of Irradiation Temperature on the Proton Response of SiGe HBTs. IEEE Transactions on Nuclear Science, 2006, 53, 3175-3181.	1.2	36
330	Sources of Phase Error and Design Considerations for Silicon-Based Monolithic High-Pass/Low-Pass Microwave Phase Shifters. IEEE Transactions on Microwave Theory and Techniques, 2006, 54, 4032-4040.	2.9	63
331	Application of RHBD Techniques to SEU Hardening of Third-Generation SiGe HBT Logic Circuits. IEEE Transactions on Nuclear Science, 2006, 53, 3400-3407.	1.2	41
332	X-Ray Irradiation and Bias Effects in Fully-Depleted and Partially-Depleted SiGe HBTs Fabricated on CMOS-Compatible SOI. IEEE Transactions on Nuclear Science, 2006, 53, 3182-3186.	1.2	12
333	A High-Slew Rate SiGe BiCMOS Operational Amplifier for Operation Down to Deep Cryogenic Temperatures. Bipolar/BiCMOS Circuits and Technology Meeting, IEEE Proceedings of the, 2006, , .	0.0	22
334	SiGe BiCMOS Precision Voltage References for Extreme Temperature Range Electronics. , 2006, , .		15
335	A Monolithic 24 GHz, 20 dBm, 14% PAE SiGe HBT Power Amplifier. , 2006, , .		12
336	SEU Error Signature Analysis of Gbit/s SiGe Logic Circuits Using a Pulsed Laser Microprobe. IEEE Transactions on Nuclear Science, 2006, 53, 3277-3284.	1.2	13